

# High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

### FEATURES AND BENEFITS

- · Differential Hall sensing rejects common-mode fields
- Patented integrated digital temperature compensation circuitry allows for near closed loop accuracy over temperature in an open loop sensor
- UL60950-1 (ed. 2) certified
   □ Dielectric Strength Voltage = 4.8 kV<sub>RMS</sub>
   □ Basic Isolation Working Voltage = 1097 V<sub>RMS</sub>
   □ Reinforced Isolation Working Voltage = 565 V<sub>RMS</sub>
- Industry-leading noise performance with greatly improved bandwidth through proprietary amplifier and filter design techniques
- Filter pin allows user to filter output for improved resolution at lower bandwidth
- $0.85 \text{ m}\Omega$  primary conductor resistance for low power loss and high inrush current withstand capability
- Low-profile SOIC16 package suitable for spaceconstrained applications
- 4.5 to 5.5 V single supply operation
- Output voltage proportional to AC or DC current

Continued on the next page...





### PACKAGE: 16-pin SOICW (suffix MA)



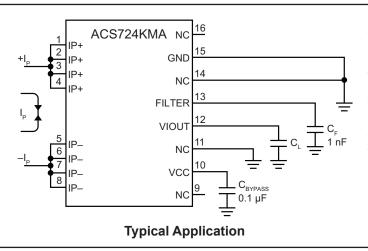
### DESCRIPTION

The Allegro<sup>™</sup> ACS724KMA current sensor IC is an economical and precise solution for AC or DC current sensing in industrial, commercial, and communication systems. The small package is ideal for space-constrained applications while also saving costs due to reduced board area. Typical applications include motor control, load detection and management, switched-mode power supplies, and overcurrent fault protection.

The device consists of a precise, low-offset, linear Hall sensor circuit with a copper conduction path located near the surface of the die. Applied current flowing through this copper conduction path generates a magnetic field which is sensed by the integrated Hall IC and converted into a proportional voltage. The current is sensed differentially in order to reject common-mode fields, improving accuracy in magnetically noisy environments. The inherent device accuracy is optimized through the close proximity of the magnetic field to the Hall transducer. A precise, proportional voltage is provided by the low-offset, chopper-stabilized BiCMOS Hall IC, which includes Allegro's patented digital temperature compensation, resulting in extremely accurate performance over temperature. The output of the device has a positive slope when an increasing current flows through the primary copper conduction path (from pins 1 through 4, to pins 5 through 8), which is the path used for current sensing. The internal resistance of this conductive path is  $0.85 \text{ m}\Omega$  typical, providing low power loss.

The terminals of the conductive path are electrically isolated from the sensor leads (pins 9 through 16). This allows the ACS724KMA current sensor IC to be used in high-side current sense applications without the use of high-side differential amplifiers or other costly isolation techniques.

Continued on the next page ...



The ACS724KMA outputs an analog signal,  $V_{IOUT}$ , that changes proportionally with the bidirectional AC or DC primary sensed current,  $I_P$ , within the specified measurement range.

The FILTER pin can be used to decrease the bandwidth in order to optimize the noise performance.

# High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

### FEATURES AND BENEFITS (continued)

- Factory-trimmed sensitivity and quiescent output voltage for improved accuracy
- Chopper stabilization results in extremely stable quiescent output voltage
- Nearly zero magnetic hysteresis
- Ratiometric output from supply voltage

### **DESCRIPTION** (continued)

The ACS724KMA is provided in a low-profile surface-mount SOIC16 package. The leadframe is plated with 100% matte tin, which is compatible with standard lead (Pb) free printed circuit board assembly processes. Internally, the device is Pb-free. The device is fully calibrated prior to shipment from the factory.

### **SELECTION GUIDE**

Part Number	I <sub>PR</sub> (A)	Sens(Typ) at V <sub>CC</sub> = 5 V (mV/A)	T <sub>A</sub> (°C)	Packing <sup>[1]</sup>
ACS724KMATR-12AB-T	±12	166	- 40 to 125	
ACS724KMATR-20AB-T	±20	100		
ACS724KMATR-30AB-T	±30	66		Tana and Baal 1000 pieces per real
ACS724KMATR-30AU-T	30	132		Tape and Reel, 1000 pieces per reel
ACS724KMATR-50AB-T	±50	40	]	
ACS724KMATR-65AB-T	±65	30.75		
	о	·	<u>`</u>	

<sup>[1]</sup> Contact Allegro for additional packing options.



# High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

### **ABSOLUTE MAXIMUM RATINGS**

Characteristic	Symbol	Notes	Rating	Units
Supply Voltage	V <sub>CC</sub>		6	V
Reverse Supply Voltage	V <sub>RCC</sub>		-0.1	V
Output Voltage	V <sub>IOUT</sub>		V <sub>CC</sub> + 0.5	V
Reverse Output Voltage	V <sub>RIOUT</sub>		-0.1	V
Maximum Continuous Current	I <sub>CMAX</sub>	$T_A = 25^{\circ}C$	60	A
Operating Ambient Temperature	T <sub>A</sub>	Range K	-40 to 125	°C
Junction Temperature	T <sub>J</sub> (max)		165	°C
Storage Temperature	T <sub>stg</sub>		–65 to 165	°C

#### **ESD RATINGS**

Characteristic	Symbol	Test Conditions	Value	Unit
Human Body Model	V <sub>HBM</sub>	Per AEC-Q100	±2	kV
Charged Device Model	V <sub>CDM</sub>	Per AEC-Q100	±1	kV

### **ISOLATION CHARACTERISTICS**

Characteristic	Symbol	Notes	Rating	Unit
Dielectric Surge Strength Test Voltage	V <sub>SURGE</sub>	Tested $\pm 5$ pulses at 2/minute in compliance to IEC 61000-4-5 1.2 µs (rise) / 50 µs (width).	10000	V
Surge Strength Test Current	I <sub>SURGE</sub>	Tested ±5 pulses at 3/minute with 8 µs (rise) / 20 µs (width)	13000	А
Dielectric Strength Test Voltage	V <sub>ISO</sub>	Agency type-tested for 60 seconds per UL 60950-1 (edition 2). Production tested at 3000 V <sub>RMS</sub> for 1 second, in accordance with UL 60950-1 (edition 2).	4800	V <sub>RMS</sub>
		Maximum approved working voltage for basic (single) isolation	1550	V <sub>PK</sub> or VDC
Working Voltage for Basic Isolation	V <sub>WVBI</sub>	according to UL 60950-1 (edition 2).	1097	V <sub>RMS</sub>
		Maximum approved working voltage for reinforced isolation	800	V <sub>PK</sub> or VDC
Working Voltage for Reinforced Isolation	V <sub>WVRI</sub>	according to UL 60950-1 (edition 2).	565	V <sub>RMS</sub>
Clearance	D <sub>cl</sub>	Minimum distance through air from IP leads to signal leads.	8.2	mm
Creepage	D <sub>cr</sub>	Minimum distance along package body from IP leads to signal leads	8.2	mm
Distance Through Insulation	DTI	Minimum internal distance through insulation	90	μm
Comparative Tracking Index	CTI	Material Group II	400 to 599	V

### THERMAL CHARACTERISTICS<sup>[1]</sup>

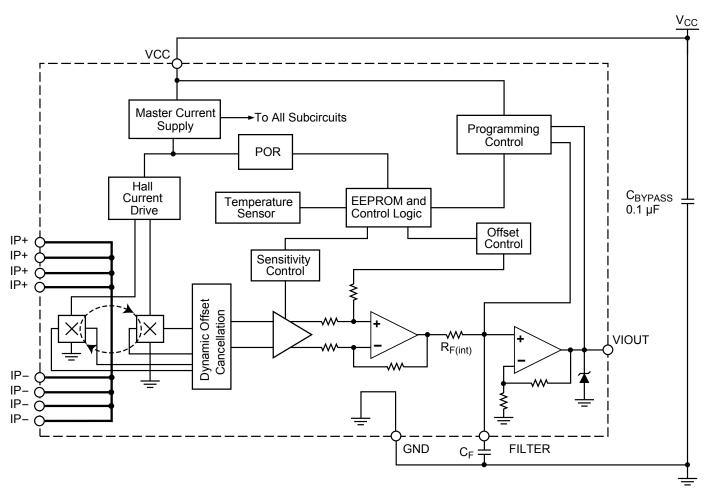
Characteristic Sy		Test Conditions	Value	Unit
Junction-to-Ambient Thermal Resistance	$R_{ extsf{ heta}JA}$	Mounted on the Allegro ASEK724/5 MA evaluation board. Performance values include the power consumed by the PCB. <sup>[2]</sup>	23	°C/W
Junction-to-Lead Thermal Resistance	$R_{ extsf{ heta}JL}$	Mounted on the Allegro ASEK724/5 MA evaluation board. <sup>[2]</sup>	5	°C/W

<sup>[1]</sup> Refer to the die temperature curves versus DC current plot (page 16). Additional thermal information is available on the Allegro website.

[2] The Allegro evaluation board has 1500 mm<sup>2</sup> of 4 oz. copper on each side, connected to pins 1 through 4 and pins 5 through 8, with thermal vias connecting the layers. Performance values include the power consumed by the PCB. Further information about board design and thermal performance also can be found in the Applications Information section of this datasheet.



# High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package





IP+ 1 IP+ 2	16 NC 15 GND	Terminal L	ist Table	
IP+ 3	14 NC	Number	Name	Description
IP+ 4	13 FILTER	1, 2, 3, 4	IP+	Terminals for current being sensed; fused internally
IP- 5	12 VIOUT	5, 6, 7, 8	IP-	Terminals for current being sensed; fused internally
IP- 6	11 NC	9, 16	NC	No internal connection; recommended to be left unconnected in order to maintain high creepage
IP- 7	10 VCC	10	VCC	Device power supply terminal
IP- 8	9 NC	11, 14	NC	No internal connection; recommened to connect to GND for the best ESD performance
Pinout Diagr	am	12	VIOUT	Analog output signal
	-	13	FILTER	Terminal for external capacitor that sets bandwidth
		15	GND	Signal ground terminal



### High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

### COMMON ELECTRICAL CHARACTERISTICS <sup>[1]</sup>: Valid through the full range of $T_A = -40^{\circ}$ C to 125°C and $V_{CC} = 5 V$ , unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Supply Voltage	V <sub>cc</sub>		4.5	5	5.5	V
Supply Current	I <sub>CC</sub>	$V_{CC}$ within $V_{CC}$ (min) and $V_{CC}$ (max)	-	10	14	mA
Output Capacitance Load	CL	VIOUT to GND	_	_	10	nF
Output Resistive Load	RL	VIOUT to GND	4.7	_	_	kΩ
Primary Conductor Resistance	R <sub>IP</sub>	$T_A = 25^{\circ}C$	_	0.85	_	mΩ
Primary Conductor Inductance	L <sub>IP</sub>	T <sub>A</sub> = 25°C	_	4	_	nH
Internal Filter Resistance [2]	R <sub>F(INT)</sub>		_	1.7	_	kΩ
Common Mode Field Rejection Ratio	CMFRR	Uniform external magnetic field	_	40	-	dB
Primary Hall Coupling Factor	G1	T <sub>A</sub> = 25°C	-	4.5	_	G/A
Secondary Hall Coupling Factor	G2	T <sub>A</sub> = 25°C	-	0.5	_	G/A
Hall Plate Sensitivity Matching	Sens <sub>MATCH</sub>	T <sub>A</sub> = 25°C	-	±1	_	%
Hysteresis	I <sub>HYS</sub>	Difference in offset after a ±40 A pulse	-	150	_	mA
Rise Time	t <sub>r</sub>	T <sub>A</sub> = 25°C, C <sub>L</sub> = 1 nF	-	3	_	μs
Propagation Delay	t <sub>pd</sub>	T <sub>A</sub> = 25°C, C <sub>L</sub> = 1 nF	-	2	_	μs
Response Time	t <sub>RESPONSE</sub>	T <sub>A</sub> = 25°C, C <sub>L</sub> = 1 nF	-	4	_	μs
Output Slew Rate	SR	T <sub>A</sub> = 25°C, C <sub>L</sub> = 1 nF	-	0.53	_	V/µs
Internal Bandwidth	BW	Small signal –3 dB, C <sub>L</sub> = 1 nF	-	120	_	kHz
Noise Density	I <sub>ND</sub>	Input-referenced noise density; $T_A = 25^{\circ}C$ , $C_L = 1 \text{ nF}$	-	450	-	µA <sub>RMS</sub> / √Hz
Noise	I <sub>N</sub>	Input-referenced noise; $C_F = 4.7 \text{ nF}$ , $C_L = 1 \text{ nF}$ , BW = 18 kHz, $T_A = 25^{\circ}C$	-	60	-	mA <sub>RMS</sub>
Nonlinearity	E <sub>LIN</sub>	Through full range of I <sub>P</sub>	_	±1		%
Sensitivity Ratiometry Coefficient	SENS_RAT_ COEF	V <sub>CC</sub> = 4.5 to 5.5 V, T <sub>A</sub> = 25°C	-	1.3	-	_
Zero-Current Output Ratiometry Coefficient	QVO_RAT_ COEF	V <sub>CC</sub> = 4.5 to 5.5 V, T <sub>A</sub> = 25°C	-	1	-	_
O stransform Maltana [2]	V <sub>OH</sub>	R <sub>L</sub> = 4.7 kΩ, T <sub>A</sub> = 25°C	V <sub>CC</sub> – 0.5	_	_	V
Saturation Voltage [3]	V <sub>OL</sub>	R <sub>L</sub> = 4.7 kΩ, T <sub>A</sub> = 25°C	-	_	0.5	V
Power-On Time	t <sub>PO</sub>	Output reaches 90% of steady-state level, $T_A = 25^{\circ}$ C, $I_P = I_{PR}$ (max) applied	-	80	-	μs
Shorted Output to Ground Current	I <sub>SC(GND)</sub>	T <sub>A</sub> = 25°C	-	3.3	-	mA
Shorted Output to V <sub>CC</sub> Current	I <sub>SC(VCC)</sub>	T <sub>A</sub> = 25°C	_	45	_	mA

<sup>[1]</sup> Device may be operated at higher primary current levels, I<sub>P</sub>, ambient temperatures, T<sub>A</sub>, and internal leadframe temperatures, provided the Maximum Junction Temperature, T<sub>J</sub>(max), is not exceeded.

 $[2] R_{F(INT)}$  forms an RC circuit via the FILTER pin. [3] The sensor IC will continue to respond to current beyond the range of I<sub>P</sub> until the high or low saturation voltage; however, the nonlinearity in this region will be worse than through the rest of the measurement range.



# High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

## xKMATR-12AB PERFORMANCE CHARACTERISTICS: $T_A$ Range K, valid at $T_A = -40^{\circ}$ C to 125°C, $V_{CC} = 5$ V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. [1]	Max.	Units
NOMINAL PERFORMANCE				·		
Current Sensing Range	I <sub>PR</sub>		-12	-	12	A
Sensitivity	Sens	I <sub>PR(min)</sub> < I <sub>P</sub> < I <sub>PR(max)</sub>	-	166	_	mV/A
Zero Current Output Voltage	V <sub>IOUT(Q)</sub>	Bidirectional; I <sub>P</sub> = 0 A	-	V <sub>CC</sub> × 0.5	_	V
ACCURACY PERFORMANC	E					
Total Output Error <sup>[2]</sup>	F	$I_P = I_{PR(max)}, T_A = 25^{\circ}C \text{ to } 125^{\circ}C$	-2.5	±1	2.5	%
	E <sub>TOT</sub>	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-	±3	_	%
TOTAL OUTPUT ERROR CO	MPONENT	S <sup>[3]</sup> : E <sub>TOT</sub> = E <sub>SENS</sub> + 100 × V <sub>OE</sub> /(Sens × I <sub>P</sub> )				
Sonoitivity Error	-	$T_A = 25^{\circ}C$ to 125°C, measured at $I_P = I_{PR(max)}$	-2	±1	2	%
Sensitivity Error	E <sub>SENS</sub>	$T_A = -40^{\circ}C$ to 25°C, measured at $I_P = I_{PR(max)}$	-	±2.8	_	%
Valtage Offeet Error	M	I <sub>P</sub> = 0 A, T <sub>A</sub> = 25°C to 125°C	-15	±5	15	mV
Voltage Offset Error	V <sub>OE</sub>	$I_{P} = 0 \text{ A}, T_{A} = -40^{\circ}\text{C} \text{ to } 25^{\circ}\text{C}$	-	±20	-	mV
LIFETIME DRIFT CHARACT	ERISTICS					
Sensitivity Error Lifetime Drift	E <sub>sens_drift</sub>		-	±1	-	%
Total Output Error Lifetime Drift	E <sub>tot drift</sub>		-	±1	_	%

<sup>[1]</sup> Typical values with +/- are 3 sigma values.

<sup>[2]</sup> Percentage of  $I_P$ , with  $I_P = I_{PR}(max)$ .



# High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

## xKMATR-20AB PERFORMANCE CHARACTERISTICS: $T_A$ Range K, valid at $T_A = -40^{\circ}$ C to 125°C, $V_{CC} = 5$ V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. <sup>[1]</sup>	Max.	Units
NOMINAL PERFORMANCE				·		·
Current Sensing Range	I <sub>PR</sub>		-20	-	20	A
Sensitivity	Sens	$I_{PR(min)} < I_P < I_{PR(max)}$	-	100	_	mV/A
Zero Current Output Voltage	V <sub>IOUT(Q)</sub>	Bidirectional; I <sub>P</sub> = 0 A	-	V <sub>CC</sub> × 0.5	_	V
ACCURACY PERFORMANC	E			· · · · · · · · · · · · · · · · · · ·		<u>^</u>
Total Output Error <sup>[2]</sup>	F	$I_P = I_{PR(max)}, T_A = 25^{\circ}C \text{ to } 125^{\circ}C$	-2.5	±1	2.5	%
	E <sub>TOT</sub>	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-	±3	_	%
TOTAL OUTPUT ERROR CO	MPONENT	S <sup>[3]</sup> : E <sub>TOT</sub> = E <sub>SENS</sub> + 100 × V <sub>OE</sub> /(Sens × I <sub>P</sub> )				
Sensitivity Error	F	$T_A = 25^{\circ}C$ to 125°C, measured at $I_P = I_{PR(max)}$	-2	±1	2	%
	E <sub>SENS</sub>	$T_A = -40^{\circ}C$ to 25°C, measured at $I_P = I_{PR(max)}$	-	±2.8	-	%
Voltage Offset Error	V	I <sub>P</sub> = 0 A, T <sub>A</sub> = 25°C to 125°C	-15	±5	15	mV
Vollage Oliset Error	V <sub>OE</sub>	$I_{P} = 0 \text{ A}, T_{A} = -40^{\circ}\text{C} \text{ to } 25^{\circ}\text{C}$	-	±20	_	mV
LIFETIME DRIFT CHARACT	ERISTICS					
Sensitivity Error Lifetime Drift	E <sub>sens_drift</sub>		_	±1	-	%
Total Output Error Lifetime Drift	E <sub>tot drift</sub>		_	±1	_	%

<sup>[1]</sup> Typical values with +/- are 3 sigma values.

<sup>[2]</sup> Percentage of  $I_P$ , with  $I_P = I_{PR}(max)$ .



# High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

## xKMATR-30AB PERFORMANCE CHARACTERISTICS: $T_A$ Range K, valid at $T_A = -40$ °C to 125°C, $V_{CC} = 5$ V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. <sup>[1]</sup>	Max.	Units
NOMINAL PERFORMANCE				· · · · · · · · · · · · · · · · · · ·		<u>^</u>
Current Sensing Range	I <sub>PR</sub>		-30	_	30	A
Sensitivity	Sens	$I_{PR(min)} < I_P < I_{PR(max)}$	-	66	_	mV/A
Zero Current Output Voltage	V <sub>IOUT(Q)</sub>	Bidirectional; I <sub>P</sub> = 0 A	_	V <sub>CC</sub> × 0.5	-	V
ACCURACY PERFORMANC	E					<u>`</u>
Total Output Error <sup>[2]</sup>	F	$I_P = I_{PR(max)}, T_A = 25^{\circ}C \text{ to } 125^{\circ}C$	-2.5	±0.8	2.5	%
	E <sub>TOT</sub>	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-	±2.7	-	%
TOTAL OUTPUT ERROR CO	MPONENT	S <sup>[3]</sup> : E <sub>TOT</sub> = E <sub>SENS</sub> + 100 × V <sub>OE</sub> /(Sens × I <sub>P</sub> )				
Sonoitivity Error	_	$T_A = 25^{\circ}C$ to $125^{\circ}C$ , measured at $I_P = I_{PR(max)}$	-2	±0.7	2	%
Sensitivity Error	E <sub>SENS</sub>	$T_A = -40^{\circ}C$ to 25°C, measured at $I_P = I_{PR(max)}$	-	±2.6	-	%
Valtage Offeet Error	V	I <sub>P</sub> = 0 A, T <sub>A</sub> = 25°C to 125°C	-15	±7	15	mV
Voltage Offset Error	V <sub>OE</sub>	$I_{P} = 0 \text{ A}, T_{A} = -40^{\circ}\text{C} \text{ to } 25^{\circ}\text{C}$	-	±15	-	mV
LIFETIME DRIFT CHARACT	ERISTICS					
Sensitivity Error Lifetime Drift	E <sub>sens_drift</sub>		-	±1	_	%
Total Output Error Lifetime Drift	E <sub>tot drift</sub>		-	±1	_	%

<sup>[1]</sup> Typical values with +/- are 3 sigma values.

<sup>[2]</sup> Percentage of  $I_P$ , with  $I_P = I_{PR}(max)$ .



# High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

## xKMATR-30AU PERFORMANCE CHARACTERISTICS: $T_A$ Range K, valid at $T_A = -40^{\circ}$ C to 125°C, $V_{CC} = 5$ V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. <sup>[1]</sup>	Max.	Units
NOMINAL PERFORMANCE			·			
Current Sensing Range	I <sub>PR</sub>		0	_	30	A
Sensitivity	Sens	$I_{PR(min)} < I_P < I_{PR(max)}$	-	132	-	mV/A
Zero Current Output Voltage	V <sub>IOUT(Q)</sub>	Unidirectional; I <sub>P</sub> = 0 A	-	V <sub>CC</sub> × 0.1	_	V
ACCURACY PERFORMANC	E			^^		
Total Output Error <sup>[2]</sup>		$I_P = I_{PR(max)}, T_A = 25^{\circ}C \text{ to } 125^{\circ}C$	-2.5	±0.7	2.5	%
	E <sub>TOT</sub>	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-	±2.5	-	%
TOTAL OUTPUT ERROR CO	MPONENT	S <sup>[3]</sup> : E <sub>TOT</sub> = E <sub>SENS</sub> + 100 × V <sub>OE</sub> /(Sens × I <sub>P</sub> )				
Sonoitivity Error	E	$T_A = 25^{\circ}C$ to 125°C, measured at $I_P = I_{PR(max)}$	-2	±0.7	2	%
Sensitivity Error	E <sub>SENS</sub>	$T_A = -40^{\circ}$ C to 25°C, measured at $I_P = I_{PR(max)}$	-	±2.5	_	%
Voltage Offect Error	N	I <sub>P</sub> = 0 A, T <sub>A</sub> = 25°C to 125°C	-15	±7	15	mV
Voltage Offset Error	V <sub>OE</sub>	$I_{P} = 0 \text{ A}, T_{A} = -40^{\circ}\text{C} \text{ to } 25^{\circ}\text{C}$	-	±20	_	mV
Lifetime Drift Characteristics				· · · · · · · · · · · · · · · · · · ·		
Sensitivity Error Lifetime Drift	E <sub>sens_drift</sub>		-	±1	_	%
Total Output Error Lifetime Drift	E <sub>tot_drift</sub>		-	±1	_	%

<sup>[1]</sup> Typical values with +/- are 3 sigma values.

<sup>[2]</sup> Percentage of  $I_P$ , with  $I_P = I_{PR}(max)$ .



# High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

## xKMATR-50AB PERFORMANCE CHARACTERISTICS: $T_A$ Range K, valid at $T_A = -40$ °C to 125°C, $V_{CC} = 5$ V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. <sup>[1]</sup>	Max.	Units
NOMINAL PERFORMANCE				· · · · · · ·		
Current Sensing Range	I <sub>PR</sub>		-50	-	50	A
Sensitivity	Sens	I <sub>PR(min)</sub> < I <sub>P</sub> < I <sub>PR(max)</sub>	-	40	_	mV/A
Zero Current Output Voltage	V <sub>IOUT(Q)</sub>	Bidirectional; I <sub>P</sub> = 0 A	_	V <sub>CC</sub> × 0.5	-	V
ACCURACY PERFORMANC	E			· · · · · · · · · · · · · · · · · · ·		
		I <sub>P</sub> = 20 A, T <sub>A</sub> = 25°C	-1.2	-	1.2	%
Total Output Error <sup>[2]</sup>	E <sub>TOT</sub>	I <sub>P</sub> = 20 A, T <sub>A</sub> = 125°C	-1.2	-	1.2	%
		$I_{P} = 20 \text{ A}, T_{A} = 0^{\circ} \text{C}$	-1.2	-	1.2	%
TOTAL OUTPUT ERROR CO	MPONENT	S <sup>[3]</sup> : E <sub>TOT</sub> = E <sub>SENS</sub> + 100 × V <sub>OE</sub> /(Sens × I <sub>P</sub> )				
		$T_A = 25^{\circ}C$ , measured at $I_P = 20 A$	-1	-	1	%
Sensitivity Error	E <sub>SENS</sub>	$T_A = 125^{\circ}C$ , measured at $I_P = 20 A$	-1	-	1	%
		$T_A = 0^{\circ}C$ , measured at $I_P = 20 A$	-1	-	1	%
		$T_A = 25^{\circ}C$	-5	-	5	mV
Voltage Offset Error	V <sub>OE</sub>	T <sub>A</sub> = 125°C	-7	-	7	mV
		$T_A = 0^{\circ}C$	-7	-	7	mV
LIFETIME DRIFT CHARACT	ERISTICS					
Sensitivity Error Lifetime Drift	E <sub>sens_drift</sub>		-	±1	_	%
Total Output Error Lifetime Drift	E <sub>tot_drift</sub>		_	±1	_	%

<sup>[1]</sup> Typical values with +/- are 3 sigma values.

<sup>[2]</sup> Percentage of  $I_P$ , with  $I_P = I_{PR}(max)$ .



# High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

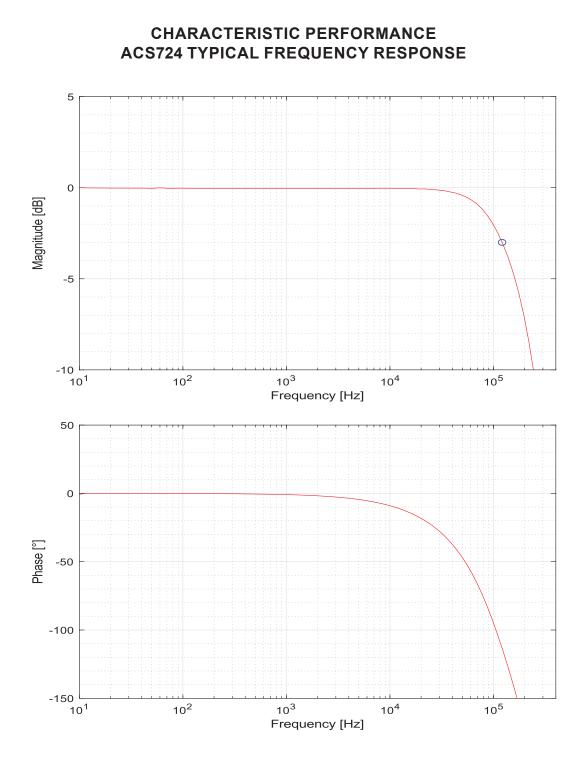
## xKMATR-65AB PERFORMANCE CHARACTERISTICS: T<sub>A</sub> Range K, valid at T<sub>A</sub> = -40°C to 125°C, V<sub>CC</sub> = 5 V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. <sup>[1]</sup>	Max.	Units
NOMINAL PERFORMANCE				· · · · · · · · · · · · · · · · · · ·		<u>^</u>
Current Sensing Range	I <sub>PR</sub>		-65	_	65	A
Sensitivity	Sens	$I_{PR(min)} < I_P < I_{PR(max)}$	-	30.75	_	mV/A
Zero Current Output Voltage	V <sub>IOUT(Q)</sub>	Bidirectional; I <sub>P</sub> = 0 A	-	V <sub>CC</sub> × 0.5	-	V
ACCURACY PERFORMANC	E			· · · · · · · · · · · · · · · · · · ·		<u>.</u>
Total Output Error <sup>[2]</sup>	E <sub>TOT</sub>	$I_P = I_{PR(max)}, T_A = 25^{\circ}C \text{ to } 125^{\circ}C$	-2.5	±1	2.5	%
		$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-	±3	_	%
TOTAL OUTPUT ERROR CO	MPONENT	S <sup>[3]</sup> : E <sub>TOT</sub> = E <sub>SENS</sub> + 100 × V <sub>OE</sub> /(Sens × I <sub>P</sub> )				
Sensitivity Error	E <sub>SENS</sub>	$T_A = 25^{\circ}C$ to 125°C, measured at $I_P = I_{PR(max)}$	-2	±1	2	%
		$T_A = -40^{\circ}$ C to 25°C, measured at $I_P = I_{PR(max)}$	-	±2.8	-	%
Voltage Offset Error	V <sub>OE</sub>	I <sub>P</sub> = 0 A, T <sub>A</sub> = 25°C to 125°C	-15	±5	15	mV
		$I_{P} = 0 \text{ A}, T_{A} = -40^{\circ}\text{C} \text{ to } 25^{\circ}\text{C}$	-	±20	-	mV
LIFETIME DRIFT CHARACT	ERISTICS					
Sensitivity Error Lifetime Drift	E <sub>sens_drift</sub>		-	±1	_	%
Total Output Error Lifetime Drift	E <sub>tot drift</sub>		-	±1	_	%

<sup>[1]</sup> Typical values with +/- are 3 sigma values.

<sup>[2]</sup> Percentage of  $I_P$ , with  $I_P = I_{PR}(max)$ .





For information regarding bandwidth characterization methods used for the ACS724, see the "Characterizing System Bandwidth" application note (https://allegromicro.com/en/insights-and-innovations/technical-documents/hall-effect-sensor-ic-publications/an%20 effective%20method%20for%20characterizing%20system%20bandwidth-an296169) on the Allegro website.



Allegro MicroSystems 955 Perimeter Road Manchester, NH 03103-3353 U.S.A. www.allegromicro.com

High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

### **RESPONSE CHARACTERISTICS DEFINITIONS AND PERFORMANCE DATA**

### **Response Time (t<sub>RESPONSE</sub>)**

The time interval between a) when the sensed input current reaches 90% of its final value, and b) when the sensor output reaches 90% of its full-scale value.

### Propagation Delay (t<sub>pd</sub>)

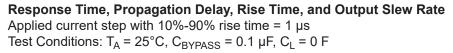
The time interval between a) when the sensed input current reaches 20% of its full-scale value, and b) when the sensor output reaches 20% of its full-scale value.

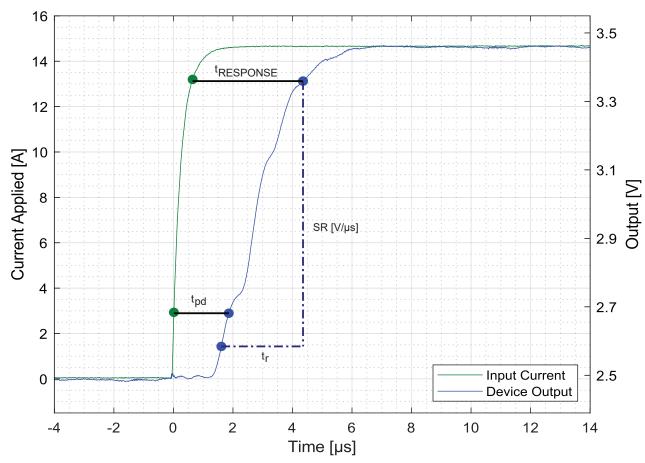
### Rise Time (t<sub>r</sub>)

The time interval between a) when the sensor reaches 10% of its full-scale value, and b) when it reaches 90% of its full-scale value.

### **Output Slew Rate (SR)**

The rate of change  $(V/\mu s)$  in the output voltage from a) when the sensor reaches 10% of its full-scale value, and b) when it reaches 90% of its full-scale value.







High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

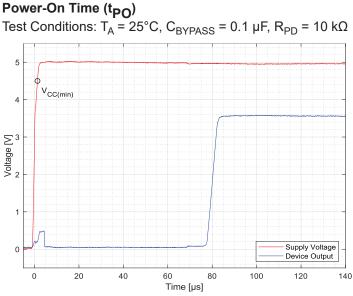
### POWER ON FUNCTIONAL DESCRIPTION AND PERFORMANCE DATA

### Power-On Time (tpO)

When the supply is ramped to its operating voltage, the device requires a finite amount of time to power its internal components before responding to an input magnetic field. Power-On Delay Time ( $t_{PO}$ ) is defined as the time interval between a) the power supply has reached its minimum specified operating voltage ( $V_{CC}(min)$ ), and b) when the sensor output has settled within  $\pm 10\%$  of its steady-state value under an applied magnetic field.

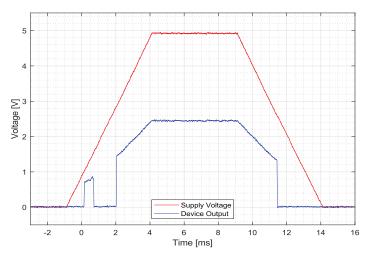
### **Power-On Profile**

After applying power, the part remains off in a known state referred to as Power-on Reset, or POR. The device stays in this state until the voltage reaches a point at which the device will remain powered. The power-on profile below illustrates the intended power on/off. A pull-down resistor was used on the output of the tested device.



#### Power-On Profile

Supply voltage ramp rate = 1V/ms Test Conditions:  $T_A = 25^{\circ}$ C,  $C_{BYPASS} = 0.1 \mu$ F,  $R_{PD} = 10 k\Omega$ 





High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

### DEFINITIONS OF ACCURACY CHARACTERISTICS

### Sensitivity (Sens)

The change in sensor IC output in response to a 1 A change through the primary conductor. The sensitivity is the product of the magnetic coupling factor (G/A) (1 G = 0.1 mT) and the linear IC amplifier gain (mV/G). The linear IC amplifier gain is programmed at the factory to optimize the sensitivity (mV/A) for the full-scale current of the device.

### Nonlinearity (E<sub>LIN</sub>)

The nonlinearity is a measure of how linear the output of the sensor IC is over the full current measurement range. The nonlinearity is calculated as:

$$E_{\text{LIN}} = \left\{ 1 - \left[ \frac{V_{\text{IOUT}}(I_{\text{PR}(\text{max})}) - V_{\text{IOUT}(\text{Q})}}{2 \times V_{\text{IOUT}}(I_{\text{PR}(\text{max})/2}) - V_{\text{IOUT}(\text{Q})}} \right] \right\} \times 100 \ (\%)$$

where  $V_{IOUT}(I_{PR(max)})$  is the output of the sensor IC with the maximum measurement current flowing through it and  $V_{IOUT}(I_{PR(max)}/2)$  is the output of the sensor IC with half of the maximum measurement current flowing through it.

### Zero Current Output Voltage (VIOUT(Q))

The output of the sensor when the primary current is zero. For a unipolar supply voltage, it nominally remains at  $0.5 \times V_{CC}$  for a bidirectional device and  $0.1 \times V_{CC}$  for a unidirectional device. For example, in the case of a bidirectional output device,  $V_{CC} = 5.0$  V translates into  $V_{IOUT(Q)} = 2.50$  V. Variation in  $V_{IOUT(Q)}$  can be attributed to the resolution of the Allegro linear IC quiescent voltage trim and thermal drift.

### Offset Voltage (V<sub>OE</sub>)

The deviation of the device output from its ideal quiescent value of 0.5 ×  $V_{CC}$  (bidirectional) or 0.1 ×  $V_{CC}$  (unidirectional) due to nonmagnetic causes. To convert this voltage to amperes, divide by the device sensitivity, Sens.

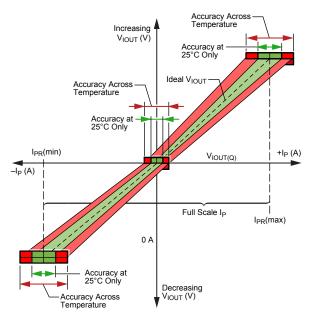
### Total Output Error (E<sub>TOT</sub>)

The difference between the current measurement from the sensor IC and the actual current ( $I_p$ ), relative to the actual current. This is equivalent to the difference between the ideal output voltage and the actual output voltage, divided by the ideal sensitivity, relative to the current flowing through the primary conduction path:

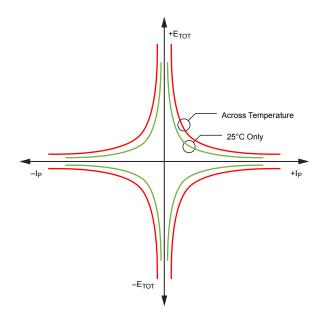
$$E_{\text{TOT}}(I_{\text{P}}) = \frac{V_{\text{IOUT\_ideal}}(I_{\text{P}}) - V_{\text{IOUT}}(I_{\text{P}})}{\text{Sens}_{\text{ideal}}(I_{\text{P}}) \times I_{\text{P}}} \times 100$$
(%)

The Total Output Error incorporates all sources of error and is a function of  $I_P$ . At relatively high currents,  $E_{TOT}$  will be mostly due to

sensitivity error, and at relatively low currents,  $E_{TOT}$  will be mostly due to Offset Voltage ( $V_{OE}$ ). In fact, at  $I_P = 0$ ,  $E_{TOT}$  approaches infinity due to the offset. This is illustrated in Figure 1 and Figure 2. Figure 1 shows a distribution of output voltages versus  $I_P$  at 25°C and across temperature. Figure 2 shows the corresponding  $E_{TOT}$  versus  $I_P$ .











# ACS724KMA High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

### **APPLICATION INFORMATION**

### **Estimating Total Error versus Sensed Current**

The Performance Characteristics tables give distribution (±3 sigma) values for Total Error at  $I_{PR(max)}$ ; however, one often wants to know what error to expect at a particular current. This can be estimated by using the distribution data for the components of Total Error, Sensitivity Error, and Offset Voltage. The ±3 sigma value for Total Error ( $E_{TOT}$ ) as a function of the sensed current ( $I_P$ ) is estimated as:

$$E_{TOT}(I_p) = \sqrt{E_{SENS}^2 + \left(\frac{100 \times V_{OE}}{Sens \times I_p}\right)^2}$$

Here,  $E_{SENS}$  and  $V_{OE}$  are the  $\pm 3$  sigma values for those error terms. If there is an average sensitivity error or average offset voltage, then the average Total Error is estimated as:

$$E_{TOT_{AVG}}(I_p) = E_{SENS_{AVG}} + \frac{100 \times V_{OE_{AVG}}}{Sens \times I_p}$$

The resulting total error will be a sum of  $E_{TOT}$  and  $E_{TOT\_AVG}$ . Using these equations and the 3 sigma distributions for Sensitivity Error and Offset Voltage, the Total Error versus sensed current (I<sub>p</sub>) is shown here for the ACS724KMATR-20AB. As expected, as one goes towards zero current, the error in percent goes towards infinity due to division by zero (refer to Figure 3).

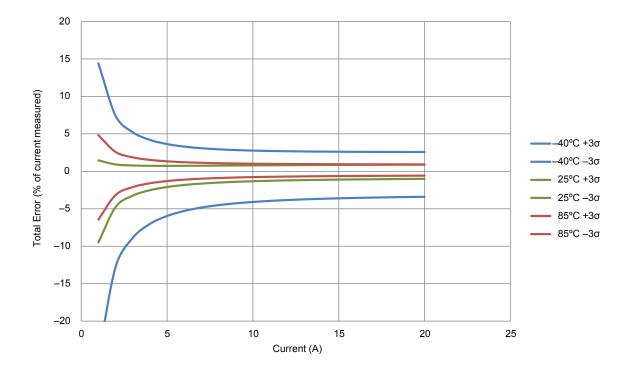


Figure 3: Predicted Total Error as a Function of Sensed Current for the ACS724KMATR-20AB



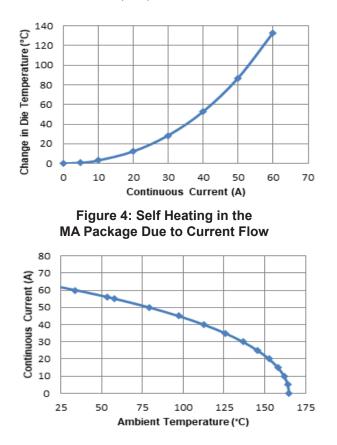
# ACS724KMA High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

### **Thermal Rise vs. Primary Current**

Self-heating due to the flow of current should be considered during the design of any current sensing system. The sensor, printed circuit board (PCB) and contacts to the PCB will generate heat as current moves through the system.

The thermal response is highly dependent on PCB layout, copper thickness, cooling techniques, and the profile of the injected current. The current profile includes peak current, current "on-time", and duty cycle. While the data presented in this section was collected with Direct-Current (DC) these numbers may be used to approximate thermal response for both AC signals and current pulses.

The plot in Figure 4 shows the measured rise in steady-state die temperature of the ACS724 versus continuous current at an ambient temperature,  $T_A$ , of 25 °C. The thermal offset curves may be directly applied to other values of  $T_A$ . Conversely, Figure 5 shows the maximum continuous current at a given  $T_A$ . Surges beyond the maximum current listed in Figure 5 are allowed given the maximum junction temperature,  $T_{J(MAX)}$  (165°C), is not exceeded.

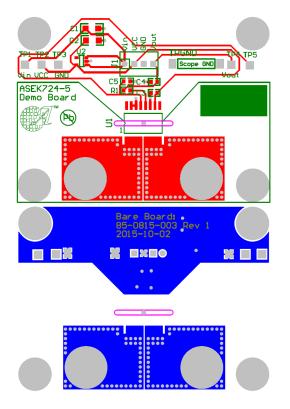




The thermal capacity of the ACS724 should be verified by the end user in the application's specific conditions. The maximum junction temperature,  $T_{J(MAX)}$  (165°C), should not be exceeded. Further information on this application testing is available in the <u>DC and</u> <u>Transient Current Capability</u> application note on the Allegro website.

### **ASEK724 Evaluation Board Layout**

Thermal data shown in Figure 4 and Figure 5 was collected using the ASEK724 Evaluation Board (TED-85-0815-003). This board includes 1500 mm<sup>2</sup> of 4 oz. copper (0.1388 mm) connected to pins 1 through 4, and to pins 5 through 8, with thermal vias connecting the layers. Top and Bottom layers of the PCB are shown below in Figure 6.



### Figure 6: Top and Bottom Layers for ASEK724 Evaluation Board

Gerber files for the ASEK724 evaluation board are available for download from our website. Please see the technical documents section of the ACS724 device webpage.



# ACS724KMA High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

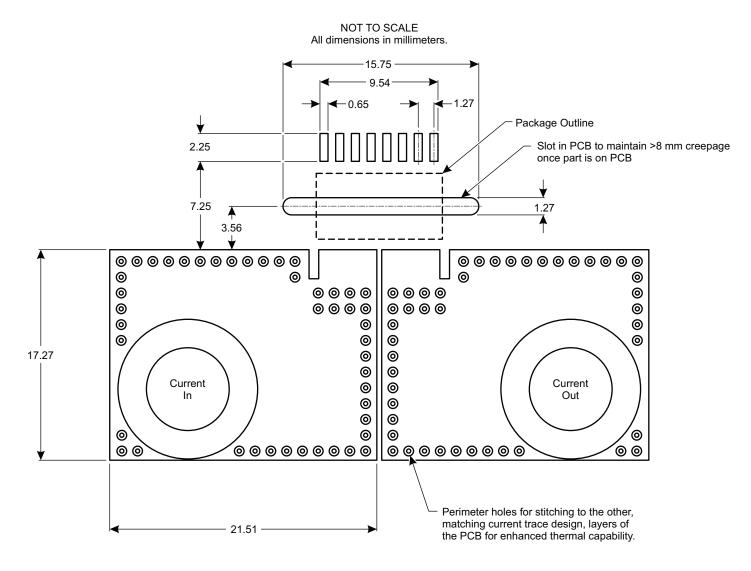


Figure 7: High-Isolation PCB Layout



# High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

### PACKAGE OUTLINE DRAWING

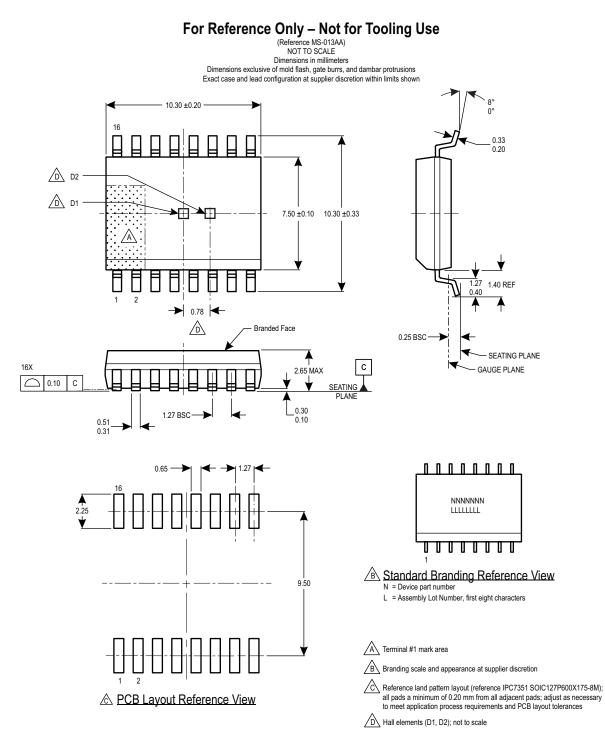


Figure 8: Package MA, 16-Pin SOICW



# High-Accuracy, Hall-Effect-Based Current Sensor IC with Common-Mode Field Rejection in High-Isolation SOIC16 Package

### **Revision History**

Number	Date	Description	
_	December 11, 2015	Initial release	
1	January 8, 2016	Added ACS724KMATR-65AB-T variant	
2	March 18, 2016	Added ACS724KMATR-30AB-T variant, UL/TUV certification; removed solder balls reference in Description	
3	April 13, 2016	Corrected Package Outline Drawing branding information (page 17).	
4	June 15, 2017	Added ACS724KMATR-12AB-T variant; corrected packing information	
5	November 27, 2017	Added Sensitivity Ratiometry Coefficient and Zero-Current Output Ratiometry Coefficient to Electrical Characteristics table (page 5).	
6	January 12, 2018	Added Dielectric Surge Strength Test Voltage to Isolation Characteristics table (page 3).	
7	January 22, 2018	Added Common Mode Field Rejection Ratio characteristic (page 5).	
8	June 22, 2018	Added Typical Frequency Response plots (page 15).	
9	December 18, 2018	Updated certificate numbers	
10	January 15, 2019	Added ACS724KMATR-65AB-T plots (page 15).	
11	June 3, 2019	Updated TUV certificate mark	
12	July 25, 2019	Updated Isolation Characteristics and Thermal Characteristics tables (page 3); added ESD Ratings table (page and Application Information section (page 20).	
13	September 9, 2019	Added Hall plate dimensions (page 22).	
14	March 5, 2020	Added Maximum Current to Absolute Maximum Ratings table (page 3); updated Isolation Characteristics Table (page 3); added ESD Ratings Table (page 3); updated Rise Time, Response Time, Propagation Delay, and Output Slew Rate test conditions (page 5); added Primary Conductor Inductance and Output Slew Rate values (page 5); updated Typical Frequency Response (page 11); added Response Characteristics Definitions and Performance Data application note (page 12); added Power On Functional Description and Performance Data (page 13); added thermal data section (page 16)	
15	May 27, 2020	Added Surge Strength Test Current to Isolation Characteristics table and updated Clearance value (page 3); Added -50AB variant (pages 2, 10)	
16	July 14, 2020	Corrected test conditions for -50AB variant performance characteristics (page 10)	
17	August 18, 2020	Corrected Total Output Error maximum values (page 10)	

Copyright 2020, Allegro MicroSystems.

Allegro MicroSystems reserves the right to make, from time to time, such departures from the detail specifications as may be required to permit improvements in the performance, reliability, or manufacturability of its products. Before placing an order, the user is cautioned to verify that the information being relied upon is current.

Allegro's products are not to be used in any devices or systems, including but not limited to life support devices or systems, in which a failure of Allegro's product can reasonably be expected to cause bodily harm.

The information included herein is believed to be accurate and reliable. However, Allegro MicroSystems assumes no responsibility for its use; nor for any infringement of patents or other rights of third parties which may result from its use.

Copies of this document are considered uncontrolled documents.

For the latest version of this document, visit our website:

### www.allegromicro.com



### **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Board Mount Current Sensors category:

Click to view products by Allegro manufacturer:

Other Similar products are found below :

 CSDD1FR
 CSNP661-007
 SCL15 10006
 L18P003S05
 T60404-B4658-X030
 LA02P021S03
 LA01M041S05
 CSNE151-003

 TLI4971A120T5UE0001XUMA1
 SIC830AED-T1-GE3
 F03P006S05L
 F03P050S05L
 CT-05
 CT-07-100
 CT-07-50
 L18P020S05
 MR-1-P5

 T60404-N4646-X400
 T60404-N4646-X661
 T60404-N4646-X662
 ACS726LLFTR-40B-T
 ACS770LCB-100B-PFF-T
 ACS711KEXLT 

 15AB-T
 DRV421RTJT
 ACS724LLCTR-30AB-T
 S23P50/100D15M1
 CSNR161005
 CSNJ481-001
 L37S200D15M
 MR-3
 T60404-N4644 

 X400
 T60404-N4644-X101
 T60404-N4646-X401
 F03P006S05
 CT-06-100
 CT-06-50
 SDV-FH5
 DC125V
 T60404-N4646-X412
 MCR1101 

 5-5
 MCA1101-5-3
 MCR1101-5-3
 ACS709LLFTR-35BB-T
 ACS710KLATR-12CB-T
 ACS724KMATR-65AB-T

 ACS758LCB-050U-PFF-T
 ACS723LLCTR-10AB-T
 ACS711KLCTR-25AB-T
 ACS713ELCTR-20A-T
 ACS724LLCTR-20AB-T